



US 20200021766A1

(19) **United States**(12) **Patent Application Publication**
Shimotsusa et al.(10) **Pub. No.: US 2020/0021766 A1**(43) **Pub. Date: Jan. 16, 2020**(54) **SOLID-STATE IMAGING DEVICE AND
MANUFACTURING METHOD THEREFOR****Publication Classification**(71) Applicant: **CANON KABUSHIKI KAISHA,**
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Fumihiko Inui, Yokohama-shi (JP)(21) Appl. No.: **16/579,058**(22) Filed: **Sep. 23, 2019****Related U.S. Application Data**(63) Continuation of application No. 15/702,097, filed on
Sep. 12, 2017, now Pat. No. 10,462,405, which is a
continuation of application No. 15/239,530, filed on
Aug. 17, 2016, now Pat. No. 9,787,931, which is a
continuation of application No. 14/555,352, filed on
Nov. 26, 2014, now Pat. No. 9,450,012, which is a
continuation of application No. 13/807,065, filed on
Dec. 27, 2012, now Pat. No. 8,928,041, filed as
application No. PCT/JP2011/003530 on Jun. 21,
2011.**Foreign Application Priority Data**

(30) Jun. 30, 2010 (JP) 2010-149476

(51) **Int. Cl.****H04N 5/378** (2006.01)**H01L 27/146** (2006.01)(52) **U.S. Cl.**CPC **H04N 5/378** (2013.01); **H01L 27/14627**
(2013.01); **H01L 27/1463** (2013.01); **H01L**
27/14632 (2013.01); **H01L 27/14634**
(2013.01); **H01L 27/1464** (2013.01); **H01L**
27/14641 (2013.01); **H01L 27/14601**
(2013.01); **H01L 27/14683** (2013.01); **H01L**
27/14612 (2013.01); **H01L 27/14636**
(2013.01); **H01L 27/14643** (2013.01); **H01L**
27/14621 (2013.01); **H01L 27/14623**
(2013.01); **H01L 27/14609** (2013.01)

(57)

ABSTRACT

A solid-state imaging device includes a first and second pixel regions. In the first pixel region, a photoelectric conversion unit, a floating diffusion region (FD), and a transferring transistor are provided. In the second pixel region, an amplifying transistor, and a resetting transistor are provided. A first element isolation portion is provided in the first pixel region, while a second element isolation portion is provided in the second pixel region. An amount of protrusion of an insulating film into a semiconductor substrate in the first element isolation portion is smaller, than that in the second element isolation portion.

